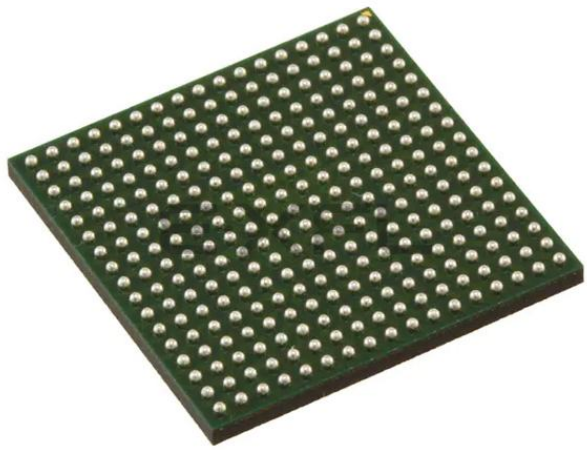

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	3120
Total RAM Bits	36864
Number of I/O	212
Number of Gates	125000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	289-TFBGA, CSBGA
Supplier Device Package	289-CSP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp125v2-csg289

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-19 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-20 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-20 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

P_{STAT} = (PDC1 or PDC2 or PDC3) + N_{BANKS} * PDC5

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

P_{CLOCK} = (PAC1 + N_{SPINE}*PAC2 + N_{ROW}*PAC3 + $N_{S\text{-}CELL}$* PAC4) * F_{CLK}

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *IGLOO PLUS FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *IGLOO PLUS FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-14.

F_{CLK} is the global clock signal frequency.

– Bit 0 (LSB) = 100%
– Bit 1 = 50%
– Bit 2 = 25%
– …
– Bit 7 (MSB) = 0.78125%
– Average toggle rate = (100% + 50% + 25% + 12.5% + . . . + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

***Table 2-19* • Toggle Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

***Table 2-20* • Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

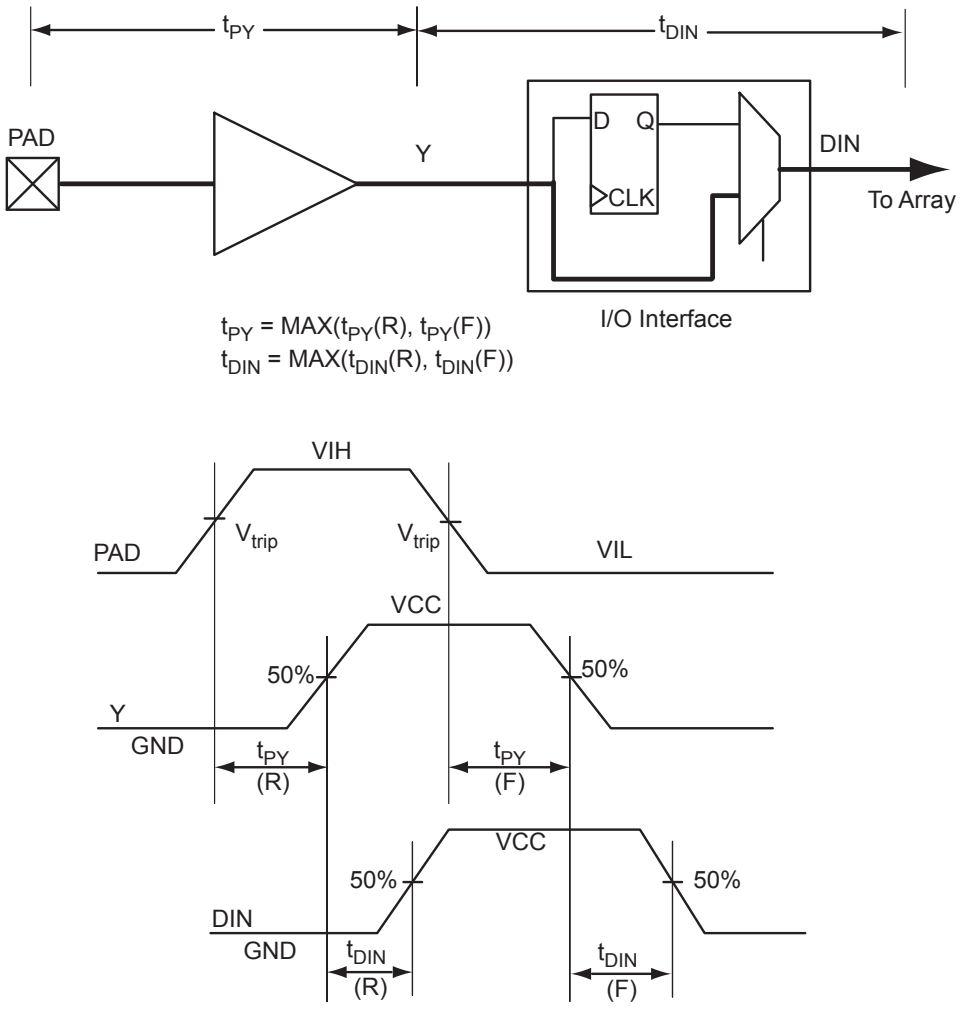


Figure 2-4 • **Input Buffer Timing Model and Delays (example)**

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option[2]	Slew Rate	VIL		VIH		VOL	VOH	IOL[1]	IOH[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range[3]	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VDD 3 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	8 mA	8 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	8	8
1.5 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4
1.2 V LVCMOS[4]	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range[4,5]	100 µA	2 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *Note that 1.2 V LVCMOS and 3.3 V LVCMOS wide range are applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to IGLOO PLUS V2 devices operating at $VCC_I \geq VCC$.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-22 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions

	Commercial[1]		Industrial[2]	
	IIL[3]	IIH[4]	IIL[3]	IIH[4]
DC I/O Standards	µA	µA	µA	µA
3.3 V LVTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCMOS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
1.2 V LVCMOS[5]	10	10	15	15
1.2 V LVCMOS Wide Range[5]	10	10	15	15

Notes:

1. *Commercial range (0°C < T_A < 70°C)*
2. *Industrial range (–40°C < T_A < 85°C)*
3. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
4. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
5. *Applicable to IGLOO PLUS V2 devices operating at VCCI ³ VCC.*

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-23 • Summary of AC Measuring Points

Standard	Measuring Trip Point (Vtrip)
3.3 V LVTTL / 3.3 V LVCMOS	1.4 V
3.3 V LVCMOS Wide Range	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
1.2 V LVCMOS	0.60 V
1.2 V LVCMOS Wide Range	0.60 V

Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY})	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12 mA	High	5 pF	–	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns
2.5 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.98	2.29	0.19	1.19	1.40	0.67	2.32	1.94	2.65	3.27	ns
1.8 V LVCMOS	8 mA	8 mA	High	5 pF	–	0.98	2.45	0.19	1.12	1.61	0.67	2.48	2.16	2.71	3.16	ns
1.5 V LVCMOS	4 mA	4 mA	High	5 pF	–	0.98	2.71	0.19	1.26	1.80	0.67	2.75	2.39	2.78	3.15	ns
1.2 V LVCMOS	2 mA	2 mA	High	5 pF	–	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns
1.2 V LVCMOS Wide Range[3]	100 µA	2 mA	High	5 pF	–	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-39 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
4 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
6 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
8 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
12 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
16 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray*

3.3 V LVCMOS Wide Range

Table 2-40 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. µA[4]	Max. µA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	103	109	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	103	109	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < V CCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

Table 2-41 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	5

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-48 • 2.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.97	4.44	0.18	1.06	1.22	0.66	4.53	4.15	1.80	1.70	ns
6 mA	STD	0.97	3.61	0.18	1.06	1.22	0.66	3.69	3.50	2.05	2.18	ns
8 mA	STD	0.97	3.61	0.18	1.06	1.22	0.66	3.69	3.50	2.05	2.18	ns
12 mA	STD	0.97	3.07	0.18	1.06	1.22	0.66	3.14	3.03	2.22	2.48	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-49 • 2.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.97	2.41	0.18	1.06	1.22	0.66	2.47	2.22	1.79	1.77	ns
6 mA	STD	0.97	1.99	0.18	1.06	1.22	0.66	2.04	1.75	2.04	2.25	ns
8 mA	STD	0.97	1.99	0.18	1.06	1.22	0.66	2.04	1.75	2.04	2.25	ns
12 mA	STD	0.97	1.77	0.18	1.06	1.22	0.66	1.81	1.51	2.22	2.56	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Applies to 1.2 V DC Core Voltage

Table 2-50 • 2.5 LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCC_I = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.98	5.04	0.19	1.19	1.40	0.67	5.12	4.65	2.22	2.36	ns
6 mA	STD	0.98	4.19	0.19	1.19	1.40	0.67	4.25	3.98	2.48	2.85	ns
8 mA	STD	0.98	4.19	0.19	1.19	1.40	0.67	4.25	3.98	2.48	2.85	ns
12 mA	STD	0.98	3.63	0.19	1.19	1.40	0.67	3.69	3.50	2.66	3.16	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-51 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.98	2.96	0.19	1.19	1.40	0.67	3.00	2.67	2.22	2.46	ns
6 mA	STD	0.98	2.52	0.19	1.19	1.40	0.67	2.56	2.18	2.47	2.95	ns
8 mA	STD	0.98	2.52	0.19	1.19	1.40	0.67	2.56	2.18	2.47	2.95	ns
12 mA	STD	0.98	2.29	0.19	1.19	1.40	0.67	2.32	1.94	2.65	3.27	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-60 • 1.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	6.07	0.18	1.16	1.62	0.66	6.19	5.53	2.13	2.02	ns
4 mA	STD	0.97	5.24	0.18	1.16	1.62	0.66	5.34	4.81	2.37	2.47	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-61 • 1.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	2.65	0.18	1.16	1.62	0.66	2.71	2.43	2.13	2.11	ns
4 mA	STD	0.97	2.29	0.18	1.16	1.62	0.66	2.33	2.00	2.37	2.57	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Applies to 1.2 V DC Core Voltage

Table 2-62 • 1.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	6.57	0.19	1.26	1.80	0.67	6.68	6.01	2.54	2.59	ns
4 mA	STD	0.98	5.72	0.19	1.26	1.80	0.67	5.81	5.27	2.79	3.05	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-63 • 1.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	3.08	0.19	1.26	1.80	0.67	3.13	2.82	2.53	2.68	ns
4 mA	STD	0.98	2.71	0.19	1.26	1.80	0.67	2.75	2.39	2.78	3.15	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

***Table 2-73* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-13 on page 2-43 for more information.*

Output Enable Register

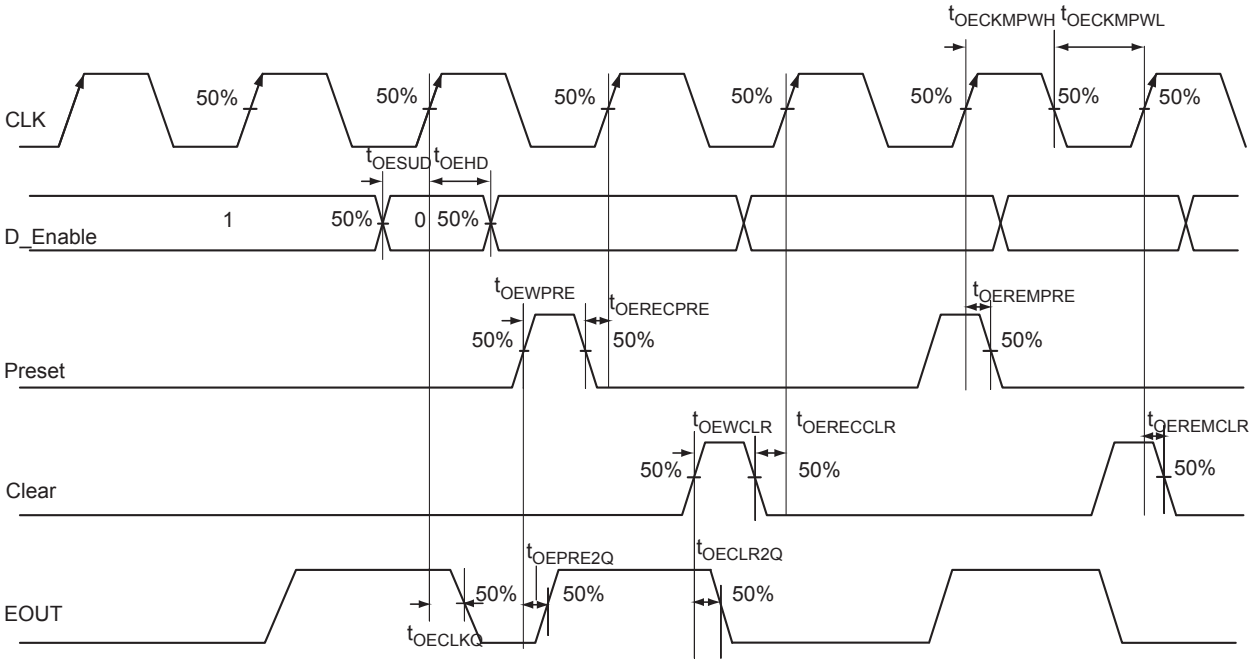


Figure 2-16 • **Output Enable Register Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-78 • **Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.68	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.33	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.84	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.91	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-88 • AGLP060 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	2.02	2.43	ns
t_{RCKH}	Input High Delay for Global Clock	2.09	2.65	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.56	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.*

Table 2-89 • AGLP125 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	2.08	2.54	ns
t_{RCKH}	Input High Delay for Global Clock	2.15	2.77	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.62	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.*

FF Flash*Freeze Mode Activation Pin

The FF pin is a dedicated input pin used to enter and exit Flash*Freeze mode. The FF pin is active low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash*Freeze mode is not used in the design, the FF pin is available as a regular I/O.

When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

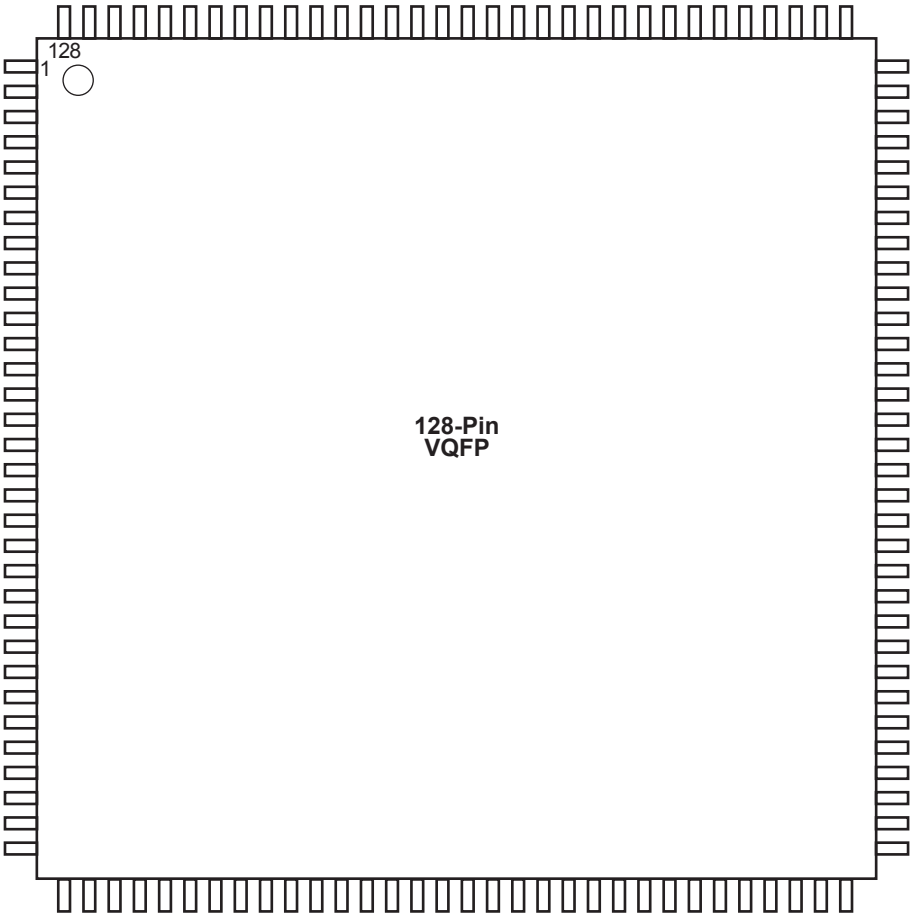
Table 3-1 shows the Flash*Freeze pin location on the available packages for IGLOO and ProASIC3L devices. The Flash*Freeze pin location is independent of device (except for a PQ208 package), allowing migration to larger or smaller IGLOO devices while maintaining the same pin location on the board. Refer to the "Flash*Freeze Technology and Low Power Modes" chapter of the *IGLOO PLUS Device Family User's Guide* for more information on I/O states during Flash*Freeze mode.

Table 3-1 • **Flash*Freeze Pin Location in IGLOO PLUS Devices**

Package	Flash*Freeze Pin
CS281	W2
CS201	R4
CS289	U1
VQ128	34
VQ176	47

4 – Package Pin Assignments

VQ128



Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

Pin information is in the "Pin Descriptions" chapter of the *IGLOO PLUS FPGA Fabric User's Guide*.

CS281	
Pin Number	AGLP125 Function
A1	GND
A2	GAB0/IO02RSB0
A3	GAC1/IO05RSB0
A4	IO09RSB0
A5	IO13RSB0
A6	IO15RSB0
A7	IO18RSB0
A8	IO23RSB0
A9	IO25RSB0
A10	VCCIB0
A11	IO33RSB0
A12	IO41RSB0
A13	IO43RSB0
A14	IO46RSB0
A15	IO55RSB0
A16	IO56RSB0
A17	GBC1/IO58RSB0
A18	GBA0/IO61RSB0
A19	GND
B1	GAA2/IO211RSB3
B2	VCCIB0
B3	GAB1/IO03RSB0
B4	GAC0/IO04RSB0
B5	IO11RSB0
B6	GND
B7	IO21RSB0
B8	IO22RSB0
B9	IO28RSB0
B10	IO32RSB0
B11	IO36RSB0
B12	IO39RSB0
B13	IO42RSB0
B14	GND
B15	IO52RSB0
B16	GBC0/IO57RSB0
B17	GBA1/IO62RSB0

CS281	
Pin Number	AGLP125 Function
B18	VCCIB1
B19	IO64RSB1
C1	GAB2/IO209RSB3
C2	IO210RSB3
C6	IO12RSB0
C14	IO47RSB0
C18	IO54RSB0
C19	GBB2/IO65RSB1
D1	IO206RSB3
D2	IO208RSB3
D4	GAA0/IO00RSB0
D5	GAA1/IO01RSB0
D6	IO10RSB0
D7	IO17RSB0
D8	IO24RSB0
D9	IO27RSB0
D10	GND
D11	IO31RSB0
D12	IO40RSB0
D13	IO49RSB0
D14	IO45RSB0
D15	GBB0/IO59RSB0
D16	GBA2/IO63RSB1
D18	GBC2/IO67RSB1
D19	IO66RSB1
E1	IO203RSB3
E2	IO205RSB3
E4	IO07RSB0
E5	IO06RSB0
E6	IO14RSB0
E7	IO20RSB0
E8	IO29RSB0
E9	IO34RSB0
E10	IO30RSB0
E11	IO37RSB0
E12	IO38RSB0

CS281	
Pin Number	AGLP125 Function
E13	IO48RSB0
E14	GBB1/IO60RSB0
E15	IO53RSB0
E16	IO69RSB1
E18	IO68RSB1
E19	IO71RSB1
F1	IO198RSB3
F2	GND
F3	IO201RSB3
F4	IO204RSB3
F5	IO16RSB0
F15	IO50RSB0
F16	IO74RSB1
F17	IO72RSB1
F18	GND
F19	IO73RSB1
G1	IO195RSB3
G2	IO200RSB3
G4	IO202RSB3
G5	IO08RSB0
G7	GAC2/IO207RSB3
G8	VCCIB0
G9	IO26RSB0
G10	IO35RSB0
G11	IO44RSB0
G12	VCCIB0
G13	IO51RSB0
G15	IO70RSB1
G16	IO75RSB1
G18	GCC0/IO80RSB1
G19	GCB1/IO81RSB1
H1	GFB0/IO191RSB3
H2	IO196RSB3
H4	GFC1/IO194RSB3
H5	GFB1/IO192RSB3
H7	VCCIB3

CS281	
Pin Number	**AGLP125 Function**
R15	IO109RSB2
R16	GDA1/IO103RSB1
R18	GDB0/IO102RSB1
R19	GDC0/IO100RSB1
T1	IO171RSB3
T2	GEC0/IO169RSB3
T4	GEB0/IO167RSB3
T5	IO157RSB2
T6	IO158RSB2
T7	IO148RSB2
T8	IO145RSB2
T9	IO143RSB2
T10	GND
T11	IO129RSB2
T12	IO126RSB2
T13	IO125RSB2
T14	IO116RSB2
T15	GDC2/IO107RSB2
T16	TMS
T18	VJTAG
T19	GDB1/IO101RSB1
U1	IO160RSB2
U2	GEA1/IO166RSB3
U6	IO151RSB2
U14	IO121RSB2
U18	TRST
U19	GDA0/IO104RSB1
V1	IO159RSB2
V2	VCCIB3
V3	GEC2/IO162RSB2
V4	IO156RSB2
V5	IO153RSB2
V6	GND
V7	IO144RSB2
V8	IO141RSB2
V9	IO140RSB2

CS281	
Pin Number	**AGLP125 Function**
V10	IO133RSB2
V11	IO127RSB2
V12	IO123RSB2
V13	IO120RSB2
V14	GND
V15	IO113RSB2
V16	GDA2/IO105RSB2
V17	TDI
V18	VCCIB2
V19	TDO
W1	GND
W2	FF/GEB2/IO163RSB2
W3	IO155RSB2
W4	IO152RSB2
W5	IO150RSB2
W6	IO147RSB2
W7	IO142RSB2
W8	IO139RSB2
W9	IO136RSB2
W10	VCCIB2
W11	IO128RSB2
W12	IO124RSB2
W13	IO119RSB2
W14	IO115RSB2
W15	IO114RSB2
W16	IO110RSB2
W17	GDB2/IO106RSB2
W18	TCK
W19	GND

CS289	
Pin Number	AGLP030 Function
G10	GND
G11	GND
G12	IO40RSB1
G13	NC
G14	IO39RSB1
G15	IO44RSB1
G16	NC
G17	GND
H1	NC
H2	GEC0/IO108RSB3
H3	NC
H4	IO112RSB3
H5	NC
H6	IO109RSB3
H7	GND
H8	GND
H9	GND
H10	GND
H11	GND
H12	NC
H13	NC
H14	IO45RSB1
H15	VCCIB1
H16	GDB0/IO48RSB1
H17	IO42RSB1
J1	NC
J2	GEA0/IO107RSB3
J3	VCCIB3
J4	IO105RSB3
J5	NC
J6	NC
J7	VCC
J8	GND
J9	GND
J10	GND
J11	VCC
J12	IO50RSB1

CS289	
Pin Number	AGLP030 Function
J13	IO43RSB1
J14	IO51RSB1
J15	IO52RSB1
J16	GDC0/IO46RSB1
J17	GDA0/IO47RSB1
K1	GND
K2	GEB0/IO106RSB3
K3	IO102RSB3
K4	IO104RSB3
K5	IO99RSB3
K6	NC
K7	GND
K8	GND
K9	GND
K10	GND
K11	GND
K12	NC
K13	NC
K14	NC
K15	IO53RSB1
K16	GND
K17	IO49RSB1
L1	IO103RSB3
L2	IO101RSB3
L3	NC
L4	GND
L5	NC
L6	NC
L7	GND
L8	GND
L9	VCC
L10	GND
L11	GND
L12	IO58RSB1
L13	IO54RSB1
L14	VCCIB1
L15	NC

CS289	
Pin Number	AGLP030 Function
L16	NC
L17	NC
M1	NC
M2	VCCIB3
M3	IO100RSB3
M4	IO98RSB3
M5	IO93RSB3
M6	IO97RSB3
M7	NC
M8	NC
M9	IO71RSB2
M10	NC
M11	IO63RSB2
M12	NC
M13	IO57RSB1
M14	NC
M15	NC
M16	NC
M17	VCCIB1
N1	NC
N2	NC
N3	IO95RSB3
N4	IO96RSB3
N5	GND
N6	NC
N7	IO85RSB2
N8	IO79RSB2
N9	IO77RSB2
N10	VCCIB2
N11	NC
N12	NC
N13	IO59RSB2
N14	NC
N15	GND
N16	IO56RSB1
N17	IO55RSB1
P1	IO94RSB3

CS289	
Pin Number	AGLP060 Function
A1	GAB1/IO03RSB0
A2	NC
A3	NC
A4	GND
A5	IO10RSB0
A6	IO14RSB0
A7	IO16RSB0
A8	IO18RSB0
A9	GND
A10	IO23RSB0
A11	IO27RSB0
A12	NC
A13	NC
A14	GND
A15	NC
A16	NC
A17	GBC0/IO30RSB0
B1	GAA1/IO01RSB0
B2	GND
B3	NC
B4	NC
B5	IO07RSB0
B6	NC
B7	VCCIB0
B8	IO17RSB0
B9	IO19RSB0
B10	IO24RSB0
B11	IO28RSB0
B12	VCCIB0
B13	NC
B14	NC
B15	NC
B16	GBC1/IO31RSB0
B17	GND
C1	IO155RSB3
C2	GAA0/IO00RSB0
C3	GAC0/IO04RSB0
C4	NC

CS289	
Pin Number	AGLP060 Function
C5	VCCIB0
C6	IO09RSB0
C7	IO13RSB0
C8	IO15RSB0
C9	IO21RSB0
C10	GND
C11	IO29RSB0
C12	NC
C13	NC
C14	NC
C15	GND
C16	GBA0/IO34RSB0
C17	IO39RSB1
D1	IO150RSB3
D2	IO151RSB3
D3	GND
D4	GAB0/IO02RSB0
D5	NC
D6	NC
D7	NC
D8	GND
D9	IO20RSB0
D10	IO25RSB0
D11	NC
D12	NC
D13	GND
D14	GBB0/IO32RSB0
D15	GBA1/IO35RSB0
D16	IO37RSB1
D17	IO42RSB1
E1	VCCIB3
E2	IO147RSB3
E3	GAC2/IO152RSB3
E4	GAA2/IO156RSB3
E5	GAC1/IO05RSB0
E6	NC
E7	IO06RSB0
E8	IO11RSB0

CS289	
Pin Number	AGLP060 Function
E9	IO22RSB0
E10	IO26RSB0
E11	VCCIB0
E12	NC
E13	GBB1/IO33RSB0
E14	GBA2/IO36RSB1
E15	GBB2/IO38RSB1
E16	VCCIB1
E17	IO44RSB1
F1	GFC1/IO140RSB3
F2	IO142RSB3
F3	IO149RSB3
F4	VCCIB3
F5	GAB2/IO154RSB3
F6	IO153RSB3
F7	NC
F8	IO08RSB0
F9	IO12RSB0
F10	NC
F11	NC
F12	NC
F13	GBC2/IO40RSB1
F14	GND
F15	IO43RSB1
F16	IO46RSB1
F17	IO45RSB1
G1	GFC0/IO139RSB3
G2	GND
G3	IO144RSB3
G4	IO145RSB3
G5	IO146RSB3
G6	IO148RSB3
G7	GND
G8	GND
G9	VCC
G10	GND
G11	GND
G12	IO48RSB1

CS289	
Pin Number	AGLP060 Function
G13	IO41RSB1
G14	IO47RSB1
G15	IO49RSB1
G16	IO50RSB1
G17	GND
H1	VCOMPLF
H2	GFB0/IO137RSB3
H3	NC
H4	IO141RSB3
H5	IO143RSB3
H6	GFB1/IO138RSB3
H7	GND
H8	GND
H9	GND
H10	GND
H11	GND
H12	GCC1/IO52RSB1
H13	IO51RSB1
H14	GCA0/IO57RSB1
H15	VCCIB1
H16	GCA2/IO58RSB1
H17	GCC0/IO53RSB1
J1	VCCPLF
J2	GFA1/IO136RSB3
J3	VCCIB3
J4	IO131RSB3
J5	IO130RSB3
J6	IO129RSB3
J7	VCC
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO59RSB1
J13	GCB1/IO54RSB1
J14	IO62RSB1
J15	IO63RSB1
J16	GCB0/IO55RSB1

CS289	
Pin Number	AGLP060 Function
J17	GCA1/IO56RSB1
K1	GND
K2	GFA0/IO135RSB3
K3	GFB2/IO133RSB3
K4	IO128RSB3
K5	IO123RSB3
K6	IO125RSB3
K7	GND
K8	GND
K9	GND
K10	GND
K11	GND
K12	IO64RSB1
K13	IO61RSB1
K14	IO66RSB1
K15	IO65RSB1
K16	GND
K17	GCC2/IO60RSB1
L1	GFA2/IO134RSB3
L2	GFC2/IO132RSB3
L3	IO127RSB3
L4	GND
L5	IO121RSB3
L6	GEC1/IO116RSB3
L7	GND
L8	GND
L9	VCC
L10	GND
L11	GND
L12	GDC1/IO72RSB1
L13	GDB1/IO74RSB1
L14	VCCIB1
L15	IO70RSB1
L16	IO68RSB1
L17	IO67RSB1
M1	IO126RSB3
M2	VCCIB3
M3	IO124RSB3

CS289	
Pin Number	AGLP060 Function
M4	IO122RSB3
M5	GEB0/IO113RSB3
M6	GEB1/IO114RSB3
M7	NC
M8	NC
M9	IO90RSB2
M10	NC
M11	IO83RSB2
M12	NC
M13	GDA1/IO76RSB1
M14	GDA0/IO77RSB1
M15	IO71RSB1
M16	IO69RSB1
M17	VCCIB1
N1	IO119RSB3
N2	IO120RSB3
N3	GEC0/IO115RSB3
N4	GEA0/IO111RSB3
N5	GND
N6	NC
N7	IO104RSB2
N8	IO98RSB2
N9	IO96RSB2
N10	VCCIB2
N11	NC
N12	NC
N13	GDB2/IO79RSB2
N14	NC
N15	GND
N16	GDB0/IO75RSB1
N17	GDC0/IO73RSB1
P1	IO118RSB3
P2	IO117RSB3
P3	GND
P4	NC
P5	NC
P6	IO106RSB2
P7	IO99RSB2

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